

ROITHNER LASERTECHNIK

A-1040 WIEN, FLEISCHMANNGASSE 9

TEL: +43 -1- 586 52 43 FAX: +43 -1- 586 41 43

e-mail: office@roithner-laser.com http://www.roithner-laser.com

RLT8405MG TECHNICAL DATA



Infrared Laserdiode

Structure: **AlGaAs double heterostructure**

Lasing wavelength: **840 nm typ.**

Typ. optical power: **5 mW**

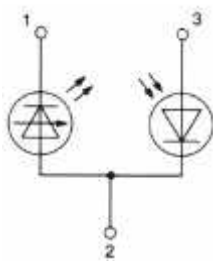
Package: **5.6 mm**

NOTE!

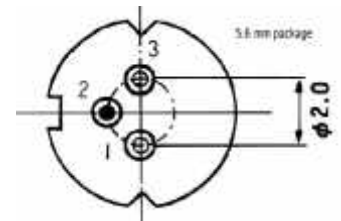
LASERDIODE
MUST BE COOLED!



PIN CONNECTION:



- 1) Laserdiode cathode
- 2) Laserdiode anode and photodiode cathode
- 3) Photodiode anode



Absolute Maximum Ratings (Tc=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power	P_o	5	mW
LD Reverse Voltage	$V_{R(LD)}$	2	V
PD Reverse Voltage	$V_{R(PD)}$	30	V
Operating Temperature	T_{op}	-10 .. +40	°C
Storage Temperature	T_{stg}	-40 .. +85	°C

Optical-Electrical Characteristics (Tc = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Threshold Current	I_{th}	cw	10	20	35	mA
Operation Current	I_{op}	$P_o = 5 \text{ mW}$	15	25	45	mA
Operation Voltage	V_{op}	$P_o = 5 \text{ mW}$	1.9	2.1	2.5	V
Lasing Wavelength	λ_p	$P_o = 5 \text{ mW}$	820	840	860	nm
Beam Divergence	$\theta_{//}$	$P_o = 5 \text{ mW}$	8	11	15	°
Beam Divergence	θ_{\perp}	$P_o = 5 \text{ mW}$	20	35	45	°
Monitor Current	I_m	$P_o = 5 \text{ mW}, V_r = 5 \text{ V}$	100	200	600	μA